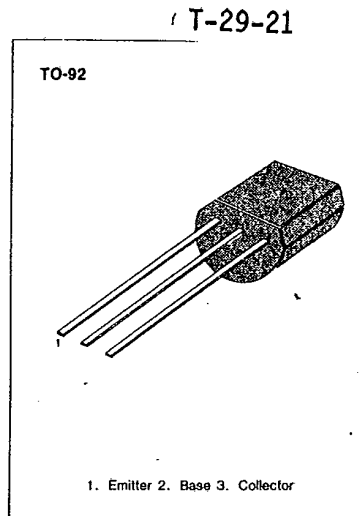


MPS6601**NPN EPITAXIAL SILICON TRANSISTOR****AMPLIFIER TRANSISTOR**

- Collector-Emitter Voltage: $V_{CE0} = 25V$
- Collector Dissipation: $P_C (\text{max}) = 625mW$

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	25	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	1000	mA
Collector Dissipation	P_C	625	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ C$

**ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)**

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 1mA, I_B = 0$	25			V
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 100\mu A, I_E = 0$	25			V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E = 10\mu A, I_C = 0$	4			V
Collector Cut-off Current	I_{CEO}	$V_{CE} = 25V, I_B = 0$			100	nA
Collector Cut-off Current	I_{CBO}	$V_{CB} = 25V, I_E = 0$			100	nA
DC Current Gain	h_{FE}	$I_C = 100mA, V_{CE} = 1V$	50			
		$I_C = 500mA, V_{CE} = 1V$	50			
		$I_C = 1000mA, V_{CE} = 1V$	30			
Collector-Emitter Saturation Voltage	$V_{CE} (\text{sat})$	$I_C = 1000mA, I_B = 100mA$			0.6	V
Current Gain Bandwidth Product	f_T	$I_C = 50mA, V_{CE} = 10V$	100			MHz
		$f = 30MHz$				
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0$			30	pF
		$f = 100KHz$				

MPS6601

NPN EPITAXIAL SILICON TRANSISTOR

T-29-21

